

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|-----------------------------|
| 1 | 820 | aluminate and semiconductor | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/08/21 15:52 |
| 4 | 129 | ((aluminate and semiconductor) and lanthanum | USPAT | 2002/08/21 16:22 |
| 5 | 120 | ((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen) | USPAT | 2002/08/21 16:22 |
| 6 | 109 | (((aluminate and semiconductor) and lanthanum) and (-nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3) | USPAT | 2002/08/21 16:22 |
| 7 | 96 | (((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate | USPAT | 2002/08/21 16:23 |
| 9 | 5 | ((((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate) and lanthanum near3 aluminum | USPAT | 2002/08/21 16:23 |
| 10 | 179 | (aluminate and semiconductor) and lanthanum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/08/21 16:22 |
| 11 | 162 | ((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/08/21 16:22 |
| 12 | 148 | (((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/08/21 16:23 |
| 13 | 96 | ((((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate | USPAT | 2002/08/21 16:23 |
| 14 | 5 | ((((aluminate and semiconductor) and lanthanum) and (nitrogen aluminum silicon oxygen)) and (dielectric electrode conduct\$3)) and substrate) and lanthanum near3 aluminum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/08/21 16:39 |
| 15 | 38 | semiconductor and lanthanum adj aluminum | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/08/21 16:40 |



- ✓ L1: (16) (aluminate and semiconductor) and (lanthanum with (nitrogen nitride
- ✓ L2: (205) (lanthanum same (nitrogen nitride\$4)) and aluminate
- ✓ L3: (5) 'La' \$3 'Al' \$3 'O' \$3 'N'
- ✓ L4: (21) La adj3 Al adj3 O\$3
- ✓ L5: (5) 'La' adj3 'Al' adj3 'O' adj3 'N'\$3
- ✓ L6: (0) (lanthanum adj aluminate) and (oxygen nitrogen aluminum)
- ✓ L7: (227) (lanthanum adj aluminate) and (oxygen nitrogen aluminum)
- ✓ L8: (132) 7 and (dielectric insulat\$3)
- ✓ L9: (125) 8 and substrate
- ✓ L10: (48) 9 and semiconductor
- ✓ L11: (4) 'La' adj2 'Al' adj2 'O' adj2 'N'
- ✓ L12: (600) La\$3Al\$3O\$3N\$3
- ✓ L14: (86) La\$2Al\$2O\$2N\$3
- ✓ L13: (47) La\$2Al\$2O\$2N\$2
- ✓ **L15: (5) La adj3 Al adj3 O adj3 N\$3**
- ✓ L16: (1) "5141802".PN.

Search

DBs: ☒ Plurals

Default operator: ☒ Highlight all hit terms initially

La adj3 Al adj3 O adj3 N\$3

☒ BRS form ☒ IS&R form ☒ Image ☒ Text ☒ HTML

| | U | 1 | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|---|--------------------------|--------------------------|---------------|------------|-------|--|------------|--------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 5403792 A | 19950404 | 5 | Low thermal conductivity ceramic and process for producing the same | 501/98.2 | |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 5262469 A | 19931116 | 6 | Oxynitride glass fiber for composite products and glass fiber-reinforced p | 524/494 | 428/373; |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 4957883 A | 19900918 | 16 | Oxynitride glass and the fiber thereof | 501/35 | 428/391; |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | EP 564257 A | 19931006 | 5 | Low thermal conductivity sialon ceramic - obtd. by mixing sialon with | | 501/56; |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | JP 63176340 A | 19880720 | 3 | Glass fibre used for reinforcing composite material - is obtd. by fusin | | 501/73; |

Start

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EAS

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10099

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EAST

9:38 AM

- ✎ L5: (17) La adj3 N adj3 O\$3
- ✎ L7: (0) La adj3 N adj3 aluminate
- ✎ L6: (97) 'La' near3 'N' near3 'O'
- ✎ L9: (3432161) La near3 N nera3 Al
- ✎ L8: (33) La adj3 N adj3 al
- ✎ L10: (9) Al adj3 La adj3 N
- ✎ L11: (62) 'Al' near3 'La' near3 'N'

- ✎ L13: (10) "197394"
- ✎ L14: (0) 6 and "197394"
- ✎ L15: (0) 2020/0197394
- ✎ L12: (82) La near3 N near3 Al
- ✎ L17: (48) 'N' near2 'Al' near2 'La'
- ✎ L16: (17) 'Al' near2 'La' near2 'N'

 **Saved**

☛ (820) aluminate and semiconductor

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Default operator: ☒ Highlight all hit terms initially

'Al' near2 'La' near2 'N'

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef ⁺ |
|---|--------------------------|--------------------------|-------------------|------------|-------|--|------------|---------------------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20020172613 A1 | 20021121 | 15 | Fe-cr-al based alloy foil and method for producing the same | 420/34 | 420/8; 428/606 |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 6475483 B1 | 20021105 | 63 | Method for in vitro proliferation of dendritic cell precursors and their use | 424/93.7 | 435/372 |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 6177351 B1 | 20010123 | 28 | Method and structure for etching a thin film perovskite layer | 438/694 | 438/710; 438/712 |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 6171970 B1 | 20010109 | 16 | Method for forming high-density integrated circuit capacitors | 438/706 | 438/710; 438/712 |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 6152400 A | 20001128 | 20 | Method for forming integrated circuit | 428/206 | 428/240 |